

Substitute Form PTO-1449  
(Modified)U.S. Department of Commerce  
Patent and Trademark OfficeAttorney Docket No.  
07977-0093002Application No.  
09/379,702**CORRECTED Information Disclosure Statement  
by Applicant**

(Use several sheets if necessary)

(37 CFR §1.98(b))

Applicant  
Hisashi Ohtani et al.Filing Date  
August 24, 1999Group Art Unit  
2815**U.S. Patent Documents**

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	A.	5,147,826	09/15/1992	Liu et al.			
	B.	5,529,937	06/25/1996	Zhang et al.			
	C.	5,569,610	10/29/1996	Zhang et al.			
	D.	5,621,224	10/05/1995	Yamazaki et al.			
	E.	5,693,541	12/02/1997	Yamazaki et al.			
	F.	5,744,824	06/02/1995	Kousai et al.			
	G.	5,756,364	11/22/1995	Tanaka et al.			
	H.	5,817,549	08/30/1995	Zhang et al.			

**Foreign Patent Documents or Published Foreign Patent Applications**

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation Yes	Translation No
	L.							
	J.							
	K.							
	L.							

**Other Documents (include Author, Title, Date, and Place of Publication)**

Examiner Initial	Desig. ID	Document
	M.	Kawazu, Japanese Journal of Applied Physics: vol. 29 no. 4 April 1990 pgs:2698-2704 "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation"
	N.	Kawazu, Japanese Journal of Applied Physics: vol. 29 no. 4 April 1990 pgs:729-738 "Initial Stage of the Interfacial Reaction between Nickel and Hydrogenated Amorphous Silicon"
	O.	Hayzelden, Journal of Applied Physics: 73 (12), 15 June 1993 pgs:8279-8289 "Silicide Formation and Silicide-Mediated Crystallization of Nickel Implanted Amorphous Silicon Thin Films"
	P.	Kuo, The Electrochemical Society Proceedings: vol.94-35 pgs:116-122 "Thin Film Technologies"
	Q.	Liu, Applied Physics Letters 55(7) 14 Aug. 1989 pgs: 660-662 "Selective area crystallization of amorphous silicon films by low-temperature rapid thermal annealing"
	R.	Cuane, Applied Surface Science 36 (1989) pgs: 597-604 "Combined CW Laser and Furnace annealing of Amorphous Si and Ge in Contact with Some Metals"
	S.	Wolf, Silicon Processing for the VLSI Era, Vol.1.2 1986 pgs: 273-275 "Passivation Layers"

Examiner Signature

Date Considered

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	AE.						
	AF.						
	AG.						
	AH.						
	AI.						
	AJ.						
	AK.						

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							Yes	No
	AL.	7-235491	09/05/1995	Japan			ABS	
	AM.							
	AN.							
	AO.							
	AP.							

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